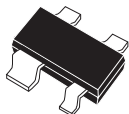


BAS28**DUAL, ISOLATED HIGH SPEED
SWITCHING DIODE****SOT-143 CASE**

CentralTM

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR BAS28 type is a ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in an epoxy molded surface mount package with isolated dual diodes, designed for high speed switching applications.

Marking code is A61.

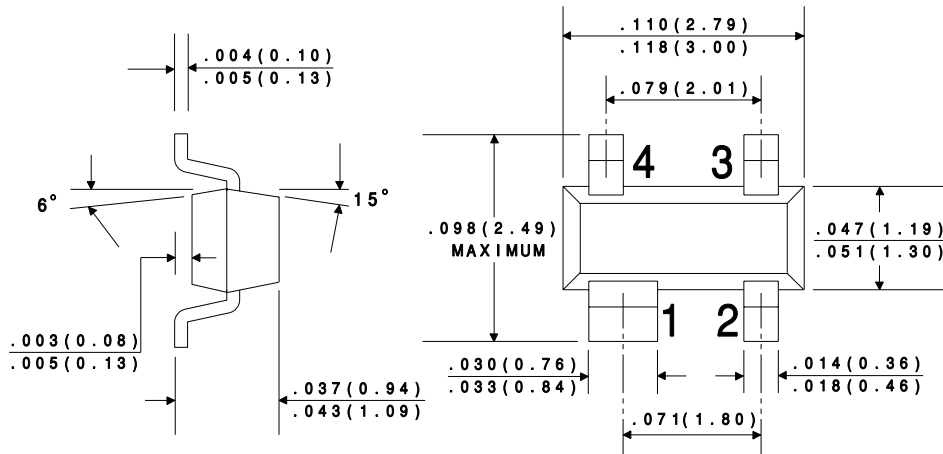
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	75	V
Peak Repetitive Reverse Voltage	V_{RRM}	85	V
Continuous Forward Current	I_F	250	mA
Peak Repetitive Forward Current	I_{FRM}	250	mA
Forward Surge Current, $t_p=1\ \mu\text{sec.}$	I_{FSM}	4000	mA
Forward Surge Current, $t_p=1\ \text{msec.}$	I_{FSM}	2000	mA
Forward Surge Current, $t_p=1\ \text{sec.}$	I_{FSM}	1000	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	θ_{JA}	357	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=25\text{V}, T_A=150^{\circ}\text{C}$		30	μA
I_R	$V_R=75\text{V}$		1.0	μA
I_R	$V_R=75\text{V}, T_A=150^{\circ}\text{C}$		50	μA
V_F	$I_F=1.0\text{mA}$		0.715	V
V_F	$I_F=10\text{mA}$		0.855	V
V_F	$I_F=50\text{mA}$		1.000	V
V_F	$I_F=150\text{mA}$		1.250	V
C_T	$V_R=0, f=1\ \text{MHz}$		2.0	pF
t_{rr}	$I_F=I_R=10\text{mA}, R_L=100\Omega, \text{Rec. to } 1.0\text{mA}$		6.0	ns
Q_S	$I_F=10\text{mA}, V_R=5.0\text{V}, R_L=500\Omega$		45	pC
V_{FR}	$I_F=10\text{mA}, t_r=20\text{ns}$		1.75	V

All dimensions in inches (mm).



LEAD CODE:

- 1) CATHODE 1
- 2) CATHODE 2
- 3) ANODE 2
- 4) ANODE 1